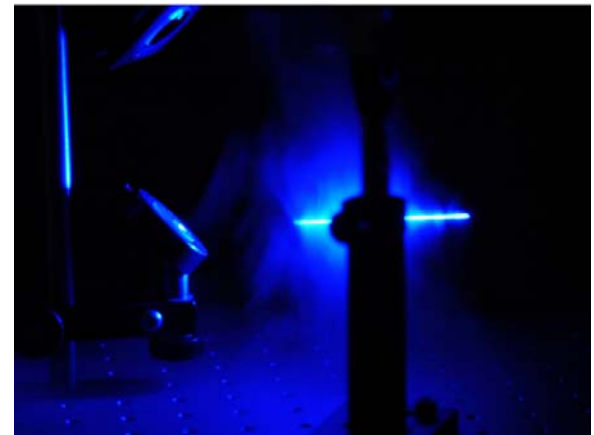
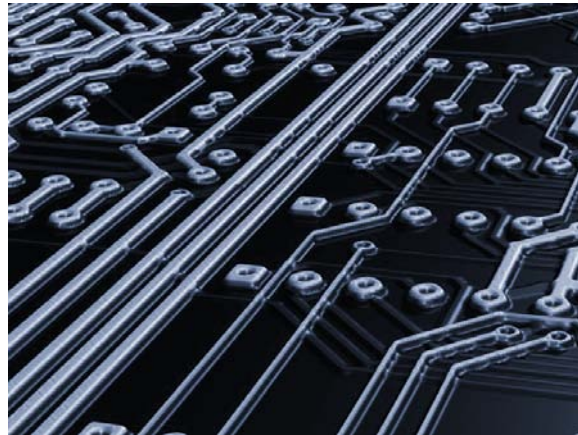


Semiconductor Intellectual Property Conference



Arthur L. Swift
President and CEO
Transmeta Corporation
<http://www.transmeta.com>



About Transmeta

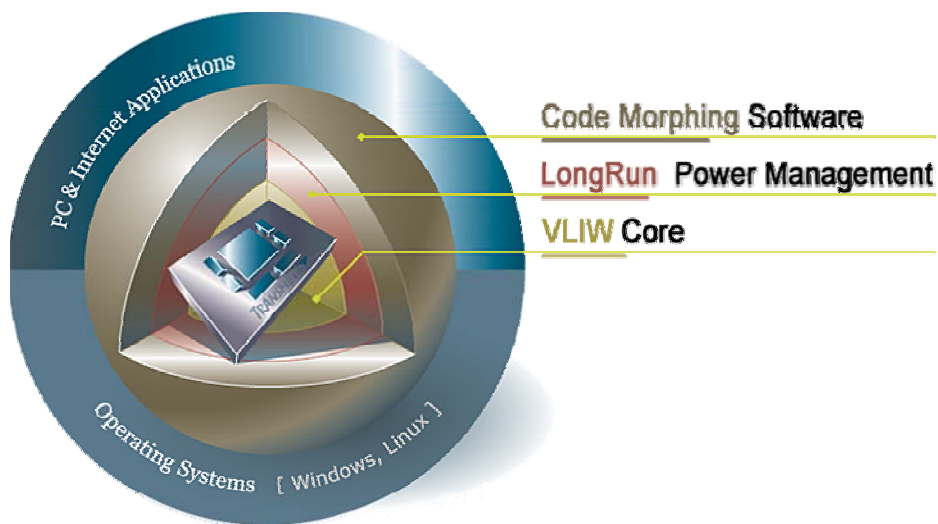
Transmeta develops and provides efficient computing technologies that improve performance, reduce power consumption and control heat generation in electronic devices

- **Transmeta Business Model**
 - Processors and Customized Processor Development
 - Technology and IP Licensing
 - Synergistic Engineering Services
- **Serves Industry Leading Customers**
 - Sony, Fujitsu, NEC, HP, Sharp ...
- **Headquartered in Santa Clara, CA**
 - Founded 1995
 - Publicly traded NASDAQ:TMTA
 - 200+ employees

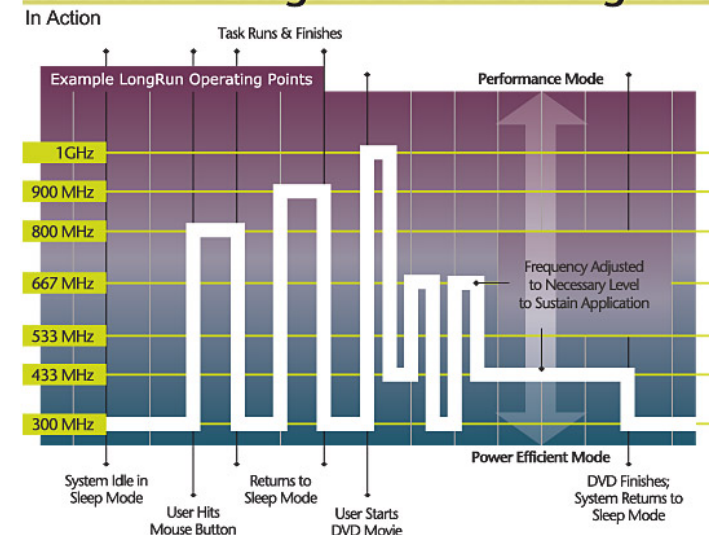


Power Management Panel: History of Innovation

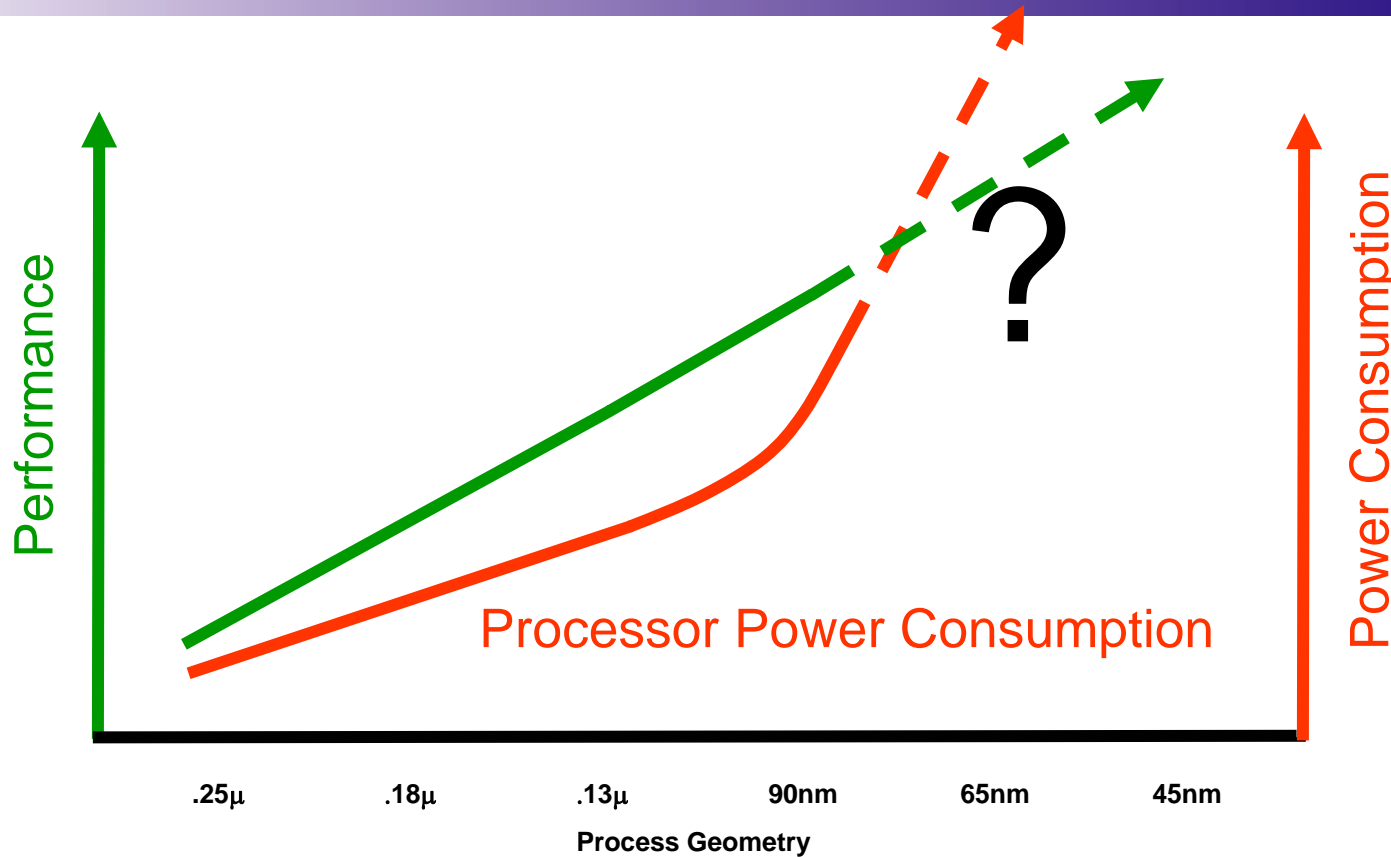
- **Transmeta led the industry with a focus on energy efficient x86-compatible processing**
 - **Looked at things differently and innovated**
 - **Processor Design – VLIW, Software/CMS**
 - **Power Management – LongRun**
 - **Enabled customers to innovate**



Transmeta™ LongRun™ Power Management



Power Management Panel: Moore's Law and Rising Power

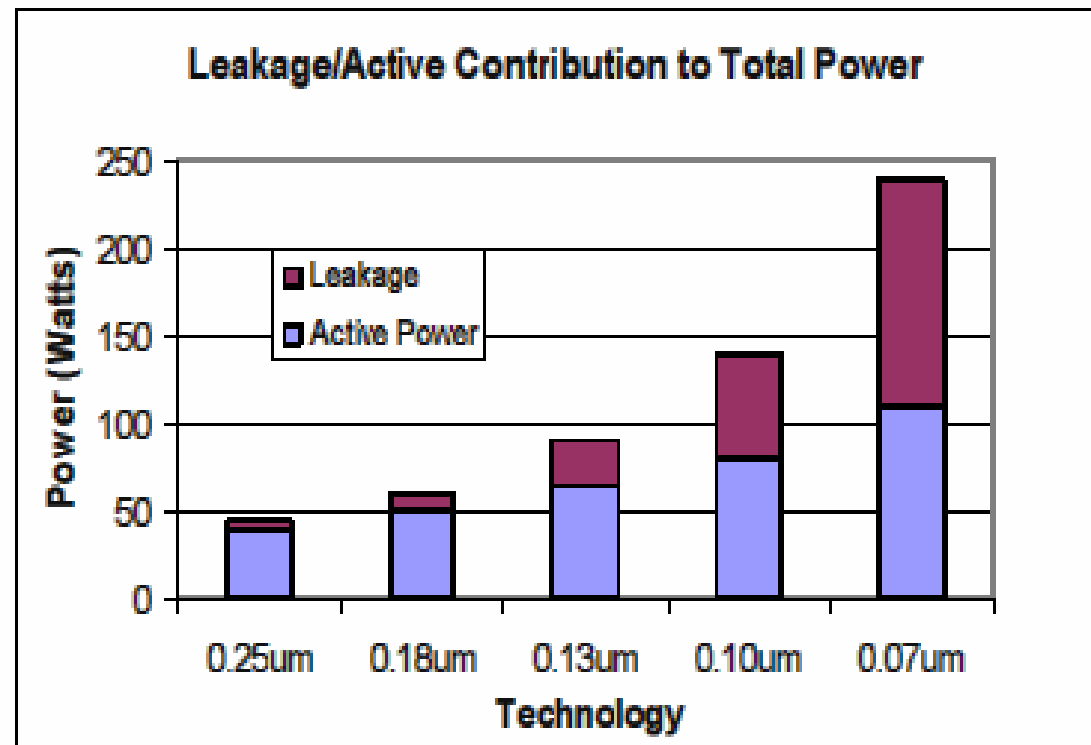


***“Moore’s law drives the industry for higher performance and lower cost, but...
The leakage power explosion and V_t fluctuation will be big stumbling blocks for
Moore’s law.”***
-Professor Takayasu Sakurai, Ph.D., University of Tokyo

Power Management Panel: Problem of Leakage

To the future, the largest inhibitor to maintaining low power - Leakage

- Main sources of leakage are
 - Source/Drain leakage
 - Gate leakage
- Other leakage mechanisms can be controlled by transistor design and process parameters.



Source: <http://www.ece.uci.edu/codes+isss/Invited/JamesLin.pdf>

Power Management Panel: Problem of Leakage



Huge concerns and extensive coverage in the last three years

“Scaling died at 130-nm”

Bernie Meyerson, CTO, IBM Systems & Technology
(Semico Conf., 1/19/04 & In-Stat/MDR Forum, 10/5/04)

“Leakage threatens CMOS scaling, panel warns”

Silicon Strategies Headline (EDA Industry Panel in San Diego, 6/8/2004)

“Power cliff, performance wall”

EE Times Headline (2/5/2004)

“Semiconductor firms find leakage a problem at 90nm”

Electronics Weekly Headline (2/8/2004)

“Power is a growing concern at 90, 65-nm nodes”

Silicon Strategies Headline (2/5/2004)

And, many more headlines, papers, articles, panels, and seminars

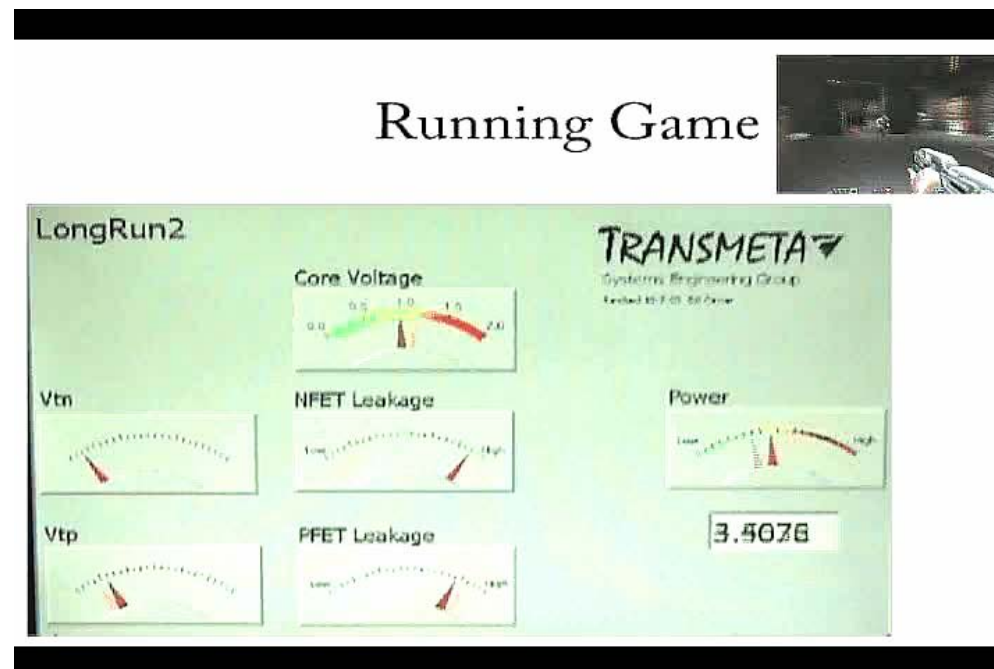
Power Management Panel: Potential Solutions to Leakage and Power Challenges

- New Materials
- Improved Processes
- Design solutions and CAD tools
- Architectural approaches
- Circuit techniques
- Non-planar devices
- Thermal control

Conventional solutions can be very complex and costly

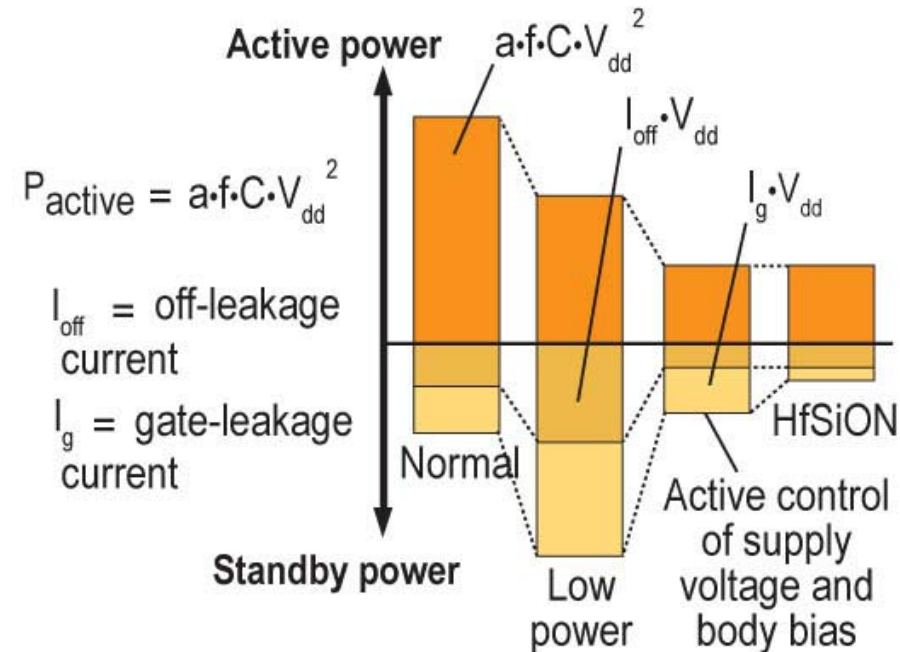
Power Management Panel: LongRun2™ Technologies

- **Mix of multiple technologies that effectively address leakage problem**
 - Implements Dynamic V_t control in a new way (Process, Circuit & S/W)
 - Complementary to other power and leakage control
 - Retrofit-able to existing “bulk silicon” designs
- **Current LongRun2 Licensees: NEC, Fujitsu and Sony**
- **First prototype demonstrated on Efficeon™ Processor, Oct. '03**



Power Management Panel: NEC Cuts 65nm Standby Power by Two Orders of Magnitude

- **NEC (LongRun2 Licensee) has cut standby current leakage by 30X to 100X using:**
 - Transmeta's LongRun2
 - High-k gate dielectric
- **As stated in the article, most of the power and leakage reduction is from LongRun2.**
- **NEC also stated that it expects to use LongRun2 enabled low-power technology in applications from low power portable phones to high-performance advanced servers.**

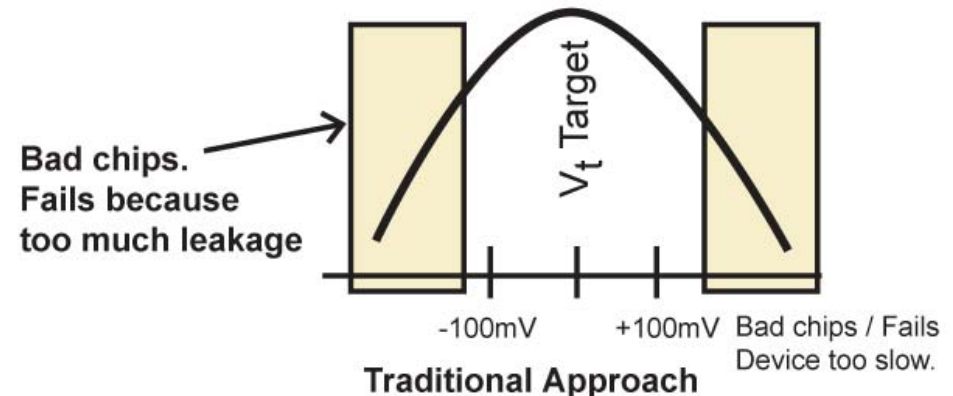


Source: Yasushi Yamagata and Kiyotaka Imai
 NEC Electronics Corp., Advanced Device Development Div.,
 Solid State Technology, November, 2004
 Initially published in Nikkei Microdevices (SST partner)

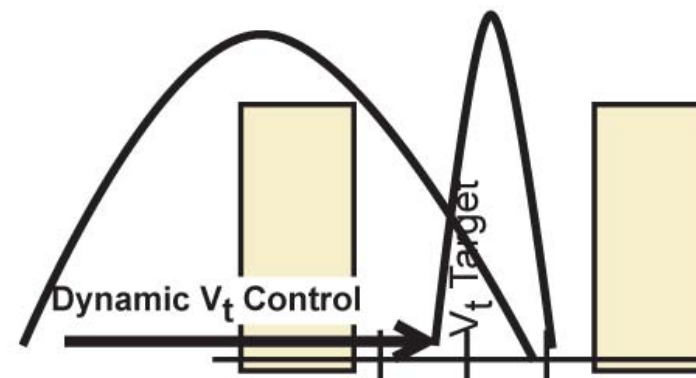
Power Management Panel: LongRun2

Improved Yield & Design for Manufacturability (DFM)

- Typically, V_t may have a wide distribution
 - Lower yields and higher costs.
- LongRun2 allows the tuning of the V_t for each die
 - Allows a very tight distribution.
 - LR2 can result in higher yields and better manufacturability through dynamic V_t control.



LongRun2 Approach



Power Management Panel: Conclusion

Continued innovation will deliver semiconductor scaling to the future

- **LongRun2 is an excellent example of a practical solution**
 - **Applicable to existing CMOS designs**
 - **Complementary to other proposed leakage control and power management solutions, such as high-k gate dielectrics.**
 - **Effectively addresses**
 - **Active power**
 - **Both main leakage mechanisms (gate leakage and source/drain leakage)**
 - **Threshold voltage fluctuations.**
 - **Improves manufacturing yields**
 - **Offers effective DFM solution for controlling V_t variability**

Thank You!

